PROCESS CPD16

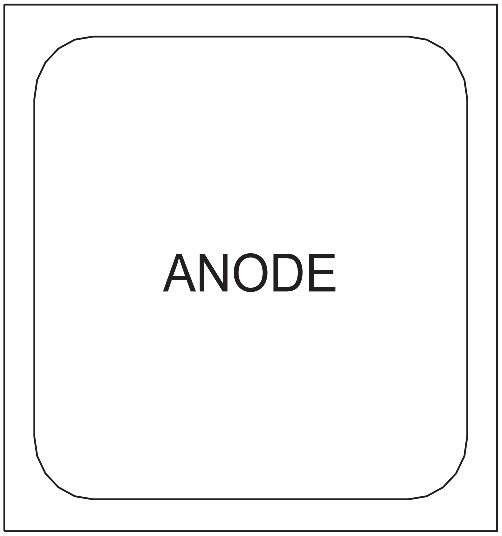
Ultra Fast Rectifier

1 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE R0

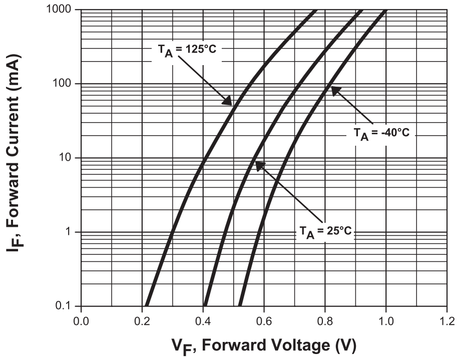
GROSS DIE PER 4 INCH WAFER
4,250

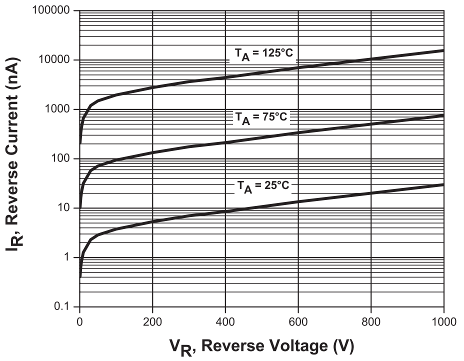
PRINCIPAL DEVICE TYPES
UES1001 thru UES1003
UF4001 thru UF4007
CMR1U-01 Series
CMR1U-01M Series

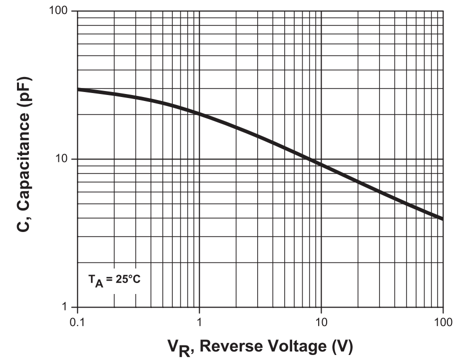
R4 (22-March 2010)

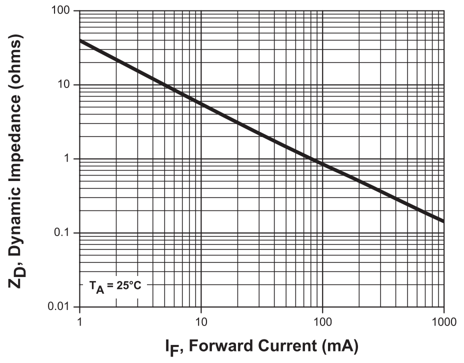
PROCESS CPD16
Typical Electrical Characteristics

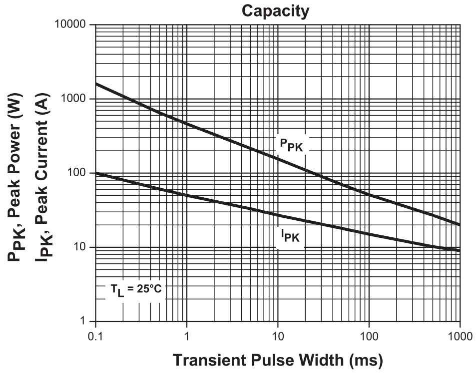
Central™ Semiconductor Corp.

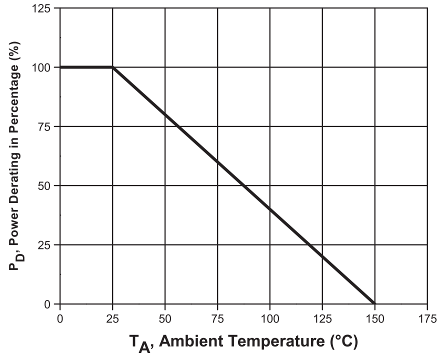

Forward Voltage


Leakage Current


Capacitance


Forward Dynamic Impedance


Transient Peak Power and Peak Current Capacity


Normalized Power Derating